



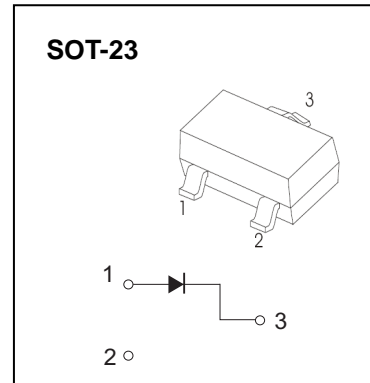
## SOT-23 Plastic-Encapsulate Diodes

**MMBD914**

**SWITCHING DIODE**

### FEATURES

High-Speed Switching Diode



**MARKING:** 5D

### Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	$V_{RM}$	100	V
Peak Repetitive Peak Reverse Voltage	$V_{RRM}$	100	V
Working Peak Reverse Voltage	$V_{RWM}$		
DC Blocking Voltage	$V_R$		
Average Rectified Output Current	$I_O$	300	mA
Peak Forward Surge Current	$I_{FSM}$	0.5	A
Power Dissipation	$P_D$	350	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{STG}$	-55~+150	°C

### Electrical Characteristics @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)}$	100			V	$I_R=100\mu A$
Forward Voltage	$V_{F1}$			715	mV	$I_F=1mA$
	$V_{F2}$			855	mV	$I_F=10mA$
	$V_{F3}$			1000	mV	$I_F=50mA$
	$V_{F4}$			1250	mV	$I_F=150mA$
Reverse Current	$I_{R1}$			1	uA	$V_R=75V$
	$I_{R2}$			25	nA	$V_R=20V$
Diode Capacitance	$C_D$			2	pF	$V_R=0, f=1MHz$
Reverse Recovery Time	$t_{rr}$			4	ns	$I_F=I_R=10mA,$ $t_{rr}=0.1 \cdot I_R$

# Typical Characteristics

# MMBD914

